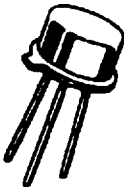
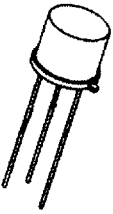


NEW ENGLAND SEMICONDUCTOR

BIPOLAR NPN TRANSISTOR TO-39/TO-5

PACKAGE	DEVICE TYPE	V _{CEO} (sus) VOLTS	I _C (max) AMPS	h _{FE} @ I _C / V _{CE} (min/max @ A/V)	V _{CE(sat)} @ I _C /I _B (V @ A/A)	P _D * WATTS	f _T (MHz)
NPN TO-39 	2N1479^	40	1.5	20-60@.2/4	1.4@.2/.02	5	1.5
	2N1480^	55	1.5	20-60@.2/4	1.4@.2/.02	5	1.5
	2N1481^	40	1.5	35-100@.2/4	1.4@.2/.01	5	1.5
	2N1482^	55	1.5	35-100@.2/4	1.4@.2/.01	5	1.5
	2N1714^	60	.75	20@0.2/5.0	2.0@.2/.02	0.8	16
	2N1715^	100	1.0	20-60@.2/5	2.0@.2/.02	1.0	16
NPN TO-5 	2N1716^	60	1.0	40-120@.2/5	2.0@.2/.02	1.0	16
	2N1717^	100	.75	40@0.2/5.0	2.0@.2/.02	0.8	16
	2N1890	60	0.5	100/300@.15/10	1.2@.05/.005	1.0	60
	2N3418^	60	3.0	20-60@1/2	.25@1/.1	7	10
	2N3419^	80	3.0	20-60@1/2	.25@1/.1	7	40
	2N3420^	60	3.0	40-120@1/2	.25@1/.1	7	40
	2N3421^	80	3.0	40-120@1/2	.25@1/.1	7	40
	2N3439^	350	1.0	40-60@.02/10	.5@.05/.004	10	15
	2N3440^	250	1.0	40-60@.02/10	.5@.05/.004	10	15

* T_C = 25°C

^h V_{CE}

^t Typical

^ Available in JAN, JANTX, JANTXV